

- L1: (6) (erwin near2 prin2).in.
- L2: (579) 365/185.14
- L3: (182) 365/185.15
- L4: (1399) 365/185.03
- L5: (617) 365/185.25
- L6: (552) 365/185.27
- L7: (1677) 365/185.29
- L8: (55489) control adj2 gate
- L9: (8608) (select or erase or program) adj2 gate
- L10: (391) nano-cluster or nanocluster or (nano adj cluster)
- L11: (2138) nanocrystal or nano-crystal or (nano adj crystal)
- L12: (3484) 8 and 9
- L14: (42) 12 and 11
- L13: (1) 12 and 10
- L19: (6) 8 and 10
- L20: (148) 8 and 11
- L22: (3989) nanocrystal\$4 or nano-crystal\$4 or (nano adj crystal\$4)
- L23: (1851) 22 not 11
- L24: (24) 8 and 23
- L31: (8) 9 and 23
- L33: (1) 22 and 2
- L36: (0) 22 and 3
- L47: (2472) 257/E27.103
- L48: (0) 47 and 10
- L49: (26) 47 and 22
- L50: (6) 49 not 20
- L51: (60) 9 and 11
- L56: (30) 22 and 4
- L57: (1) 22 and 5
- L58: (2) 22 and 6
- L59: (20) 22 and 7
- L60: (599) 22 and 257/
- L62: (135) 60 and 8
- L63: (54) 60 and 9
- L64: (97) 62 not 63

STN/EXPLORE

Previous Next Queue Clear

DBs USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM\_TDB

Default operator: OR

☒ Plurals

☒ Highlight all hit terms initially

	U	1	2	Document ID <sup>a</sup>	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Cla	Inventor	S	C	P	E
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5958936 A	19990928	9	Multi-state flash memory cell and method for programming signals	365/185.33	257/E29.301; 257/E29.302		Forbes, Leonard	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6166401 A	20001226	13	Flash memory with microcrystalline silicon carbide film	257/77	257/314; 257/321		Forbes, Leonard	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6400610 B1	20020604	8	Memory device including isolated storage elements that utilize hole n	365/185.29	257/E21.209; 257/E29.302		Sadd, Michael Alan	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6563728 B2	20030513	21	Semiconductor memory device and method for operation thereof	365/63	257/E21.679; 257/E21.682		Kobayashi, Toshio	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6654282 B2	20031125	26	Nonvolatile semiconductor memory device	365/185.05	257/E27.103; 365/185.11		Kanai, Masahiro	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6708599 B1	20040316	13	Multi-bit non-volatile memory device and method thereof	438/261	438/287		Sadd, Michael et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>